

CLAIMS

1. A SiC edge ring, comprising:
a first deposition part having a plasma-damaged portion and a non-damaged portion and comprising SiC; ~~and~~
a second deposition part formed on the first deposition part and comprising SiC,
wherein a boundary between the damaged portion of the first deposition part and the second deposition part includes an uneven surface; and
wherein the first deposition part, the second deposition part, or both the first deposition part and the second deposition part includes at least two separated structures.
2. The SiC edge ring according to claim 1, wherein the uneven surface is formed by plasma-etching.
3. The SiC edge ring according to claim 1, wherein a height difference between a highest point and a lowest point of an uneven surface formed from a portion having the same height before being exposed to the plasma to be damaged, in the uneven surface, is 0.5 mm to 3 mm.
4. The SiC edge ring according to claim 1, wherein a surface roughness of the uneven surface is 0.1 μm to 2.5 μm .
5. The SiC edge ring according to claim 1, wherein the first deposition part and the second deposition part have different transmittances.
6. The SiC edge ring according to claim 1, wherein the first deposition part includes at least any one selected from a group consisting of graphite, reaction sintered SiC, normal-pressure sintered SiC, hot press SiC, recrystallized SiC, CVD SiC, TaC, and YaC.
7. The SiC edge ring according to claim 6, wherein a difference in transmittances between the first deposition part and the second deposition part is larger than a difference in transmittances between a plurality of stacked layers in the second deposition part.
8. The SiC edge ring according to claim 1, wherein the first deposition part

includes a plurality of stacked layers and transmittance gradually changes at the boundary between the plurality of stacked layers of the first deposition part.

9. The SiC edge ring according to claim 1, further comprising:
a third deposition part formed on the second deposition part,
wherein a boundary surface between the second deposition part and the third deposition part includes an uneven surface.

10. The SiC edge ring according to claim 9, wherein the first deposition part, the second deposition part, and the third deposition part have different transmittances, and the third deposition part formed on the second deposition part is further included and in a cross-section of the reproduced SiC edge ring, a boundary line between the first deposition part and the second deposition part and a boundary line between the second deposition part and the third deposition part include a section in which the boundary lines are parallel.

~~11. The SiC edge ring according to claim 1, wherein the first deposition part includes at least two separated structures.~~

~~12. The SiC edge ring according to claim 1, wherein the second deposition part includes at least two separated structures.~~

~~13~~11. The SiC edge ring according to claim ~~11~~ or ~~12~~, wherein the at least two separated structures have the same transmittance.

~~14~~12. The SiC edge ring according to claim 1, wherein the first deposition part forms one structure which is not separated, a cross-section of the first deposition part includes a first region to a third region from an outer side surface of the SiC edge ring to an inner side surface, and an average thickness t_1 of the first region, an average thickness t_2 of the second region, and an average thickness t_3 of the third region is $t_1 > t_3 > t_2$.

~~15~~13. The SiC edge ring according to claim 1, wherein an average thickness of the second deposition part is 0.5 mm to 3 mm.

~~16~~14. The SiC edge ring according to claim 1, wherein the uneven surface is subjected

to a surface processing treatment before forming the second deposition part.